Characteristics **Kennwerte**

		T_j = 25°C	Min.	Typ.	Max.
DC current gain – Kollektor-Basis-Stromverhältnis					
V_{CE} = 5 V, I_C = 10 µA	Group A	h_{FE}	–	90	–
	Group B		–	150	–
	Group C		–	270	–
V_{CE} = 5 V, I_C = 2 mA	Group A	h_{FE}	110	180	220
	Group B		200	290	450
	Group C		420	520	800
Collector-Emitter saturation voltage – Kollektor-Sättigungsspannung [1])					
I_C = 10 mA, I_B = 0.5 mA		V_{CEsat}	–	90 mV	250 mV
I_C = 100 mA, I_B = 5 mA			–	200 mV	600 mV
Base-Emitter saturation voltage – Basis-Sättigungsspannung [2])					
I_C = 10 mA, I_B = 0.5 mA		V_{BEsat}	–	700 mV	–
I_C = 100 mA, I_B = 5 mA			–	900 mV	–
Base-Emitter-voltage – Basis-Emitter-Spannung [2])					
V_{CE} = 5 V, I_C = 2 mA		V_{BE}	580 mV	660 mV	700 mV
V_{CE} = 5 V, I_C = 10 mA			–	–	720 mV
Collector-Base cutoff current – Kollektor-Basis-Reststrom					
V_{CB} = 30 V, (E open)		I_{CBO}	–	–	15 nA
V_{CE} = 30 V, T_j = 125°C, (E open)			–	–	5 µA
Emitter-Base cutoff current					
V_{EB} = 5 V, (C open)		I_{EBO}	–	–	100 nA
Gain-Bandwidth Product – Transitfrequenz					
V_{CE} = 5 V, I_C = 10 mA, f = 100 MHz		f_T	–	300 MHz	–
Collector-Base Capacitance – Kollektor-Basis-Kapazität					
V_{CB} = 10 V, I_E = i_e = 0, f = 1 MHz		C_{CBO}	–	3.5 pF	6 pF
Emitter-Base Capacitance – Emitter-Basis-Kapazität					
V_{EB} = 0.5 V, I_C = i_c = 0, f = 1 MHz		C_{EBO}	–	9 pF	–
Thermal resistance junction to ambient Wärmewiderstand Sperrschicht – Umgebung		R_{thA}	< 420 K/W [2])		

1 Tested with pulses t_p = 300 µs, duty cycle ≤ 2%
Gemessen mit Impulsen t_p = 300 µs, Schaltverhältnis ≤ 2%

2 Mounted on P.C. board with 3 mm² copper pad at each terminal
Montage auf Leiterplatte mit 3 mm² Kupferbelag (Lötpad) an jedem Anschluss

